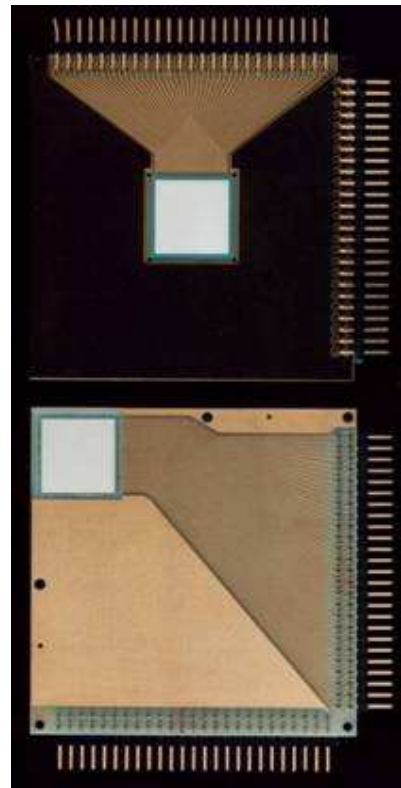


**SPECIALIST DETECTORS FOR NUCLEAR PHYSICS**

SILICON DETECTOR TYPE:	DOUBLE SIDED DC COUPLED MICROSTRIP DETECTOR		
TECHNOLOGY:	3 INCH SILICON		
DESIGN:	Ion implanted totally depleted DC coupled structure. Excellent timing resolutions have been achieved in Heavy Ion Physics experiments. Detector available centrally located and corner located in package. Compatible with Rutherford Laboratory Hybrid electronics.		
ACTIVE AREA:	2.56 cm <sup>2</sup> 16 x 16 mm <sup>2</sup>		
N <sup>o</sup> of CHANNELS:	96 (48/side)		
ELEMENT PITCH:	335 μm		
READOUT:	100 %		
THICKNESS:	60μm	140μm	300μm
		500 μm	
THICKNESS TOLERANCE:	± 15 μm		
THICKNESS UNIFORMITY:	± 5 μm		
FULL DEPLETION (FD):	30 V typical, 50 V maximum		
OPERATING VOLTAGE:	FD to 2 x FD		
ELEMENT CAPACITANCE:	1 pF typical		
ELEMENT LEAKAGE CURRENT:	3 nA typically, 30 nA maximum		
TOTAL LEAKAGE CURRENT:	100 nA typically, 300 nA maximum		
INTERSTRIP RESISTANCE JUNCTION SIDE:	10 MΩ minimum, 100 MΩ typically.		
INTERSTRIP RESISTANCE OHMIC SIDE:	100 MΩ minimum, 1 MΩ typically.		
GUARD RING:	Yes		
METALLISATION:	3000 Å		
METALLISATION TOLERANCE:	± 1000 Å		
OXIDE WIDTH:	500 μm		
RADIATION HARDNESS:	1 nA/cm <sup>2</sup> /100 Rads		
PACKAGE:	PCB with central or corner detection		
FAN OUT:	Standard		
AMPLIFIER INTERFACE:	16 Channel Hybrid		
MINIMUM ACCEPTANCE LEVEL:	100 %		
ADDITIONAL OPTION:	Silox scratch proof coating		
EXPERIMENTS:	SERC Daresbury Charissa/University of Edinburgh		



QUALITY ASSURANCE :ISO900

